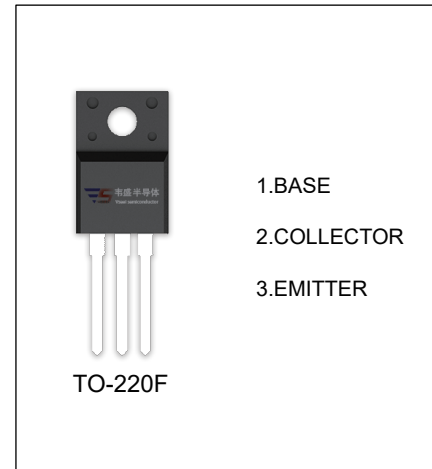


2SD2137 TRANSISTOR (NPN)

FEATURES

- High Forward Current Transfer Ratio h_{FE} which Has Satisfactory Linearity
- Low Collector to Emitter Saturation Voltage $V_{CE(sat)}$
- Allowing Supply with the Radial Taping



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Power Dissipation	2	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1\text{mA}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=30\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1\text{mA}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			100	μA
Collector cut-off current	I_{CEO}	$V_{CE}=30\text{V}, I_B=0$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=4\text{V}, I_C=1\text{A}$	70		320	
	$h_{FE(2)}$	$V_{CE}=4\text{V}, I_C=3\text{A}$	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3\text{A}, I_B=375\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=4\text{V}, I_C=3\text{A}$			1.8	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=0.2\text{A}, f=10\text{MHz}$		30		MHz
Switch time	Turn-on time	$V_{CC}=50\text{V}, I_C=1\text{A}, I_{B1}=-I_{B2}=0.1\text{A}$		0.3		μs
	Storage time			2.5		μs
	Fall time			0.2		μs

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	P	O
Range	70-150	120-250	160-320